

SILVACO
FROM ATOMS TO SYSTEMS

SPICE Modeling Solutions For Display Technologies

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December 2020

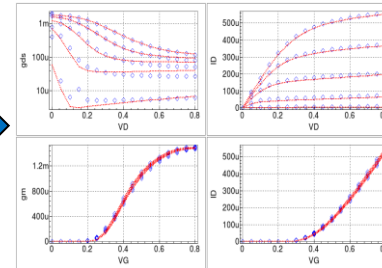
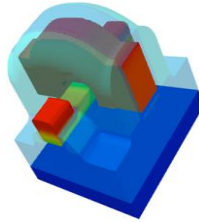
Outline

- Silvaco Modeling Solutions
- TFT Models in SmartSpice and Utmost IV
- TFT Frequency Dispersion Effect
- OLED SPICE Modeling
- Micro-LED SPICE Modeling
- Conclusions

Introduction: SPICE Modeling Software and Services

• UTMOST IV

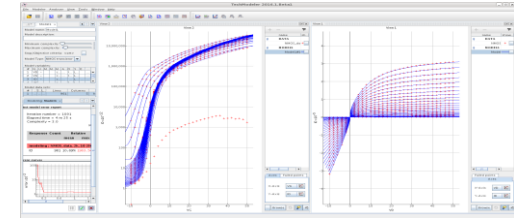
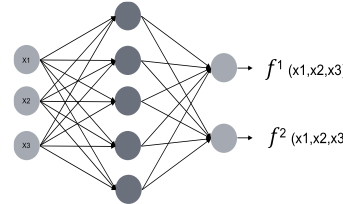
- Extract and validate SPICE parametric models
- Data from measurement equipment or TCAD
- High-speed simulation
- Verilog-A and macromodel support



```
.MODEL NFE1 NMOS (
+LEVEL = 72
+CGSND = 0
+ICGND = 0
+IIMGD = 0
+PASCND = 0
+SCGND = 0
+LIS = 0
+LIS = 1
+LIS = 0
+DELTAUCV = 0
+FEFC = 1
+FRIG = 4.3632
+KASIB = 4.05
+KCSIB = 2.86e+25
+KLSIB = 0.0186507
+KSCIB = 0.1102936
+KTE = 0.6
VERSION = 108
GEOMD = 0
IGMND = 0
JGMND = 0
SUGMND = 0
LIST = 0
DEC = 0
BOT = 1.112e-09
NFE1 = 2.1e-08
DELTA = 0
BRDY = 1e+20
EPRSD = 3.9
NFE1B = 1.1e+16
NGATE = 0
CIT = 0.0026446
CSCIB = 0.003
PRN = 0.35
```

• TechModeler

- Advanced Machine Learning approach to modeling using approximation functions
- Complement to UTMOST IV
- Modeling solution for novel/special devices and phenomena (e.g., NBI Stress)

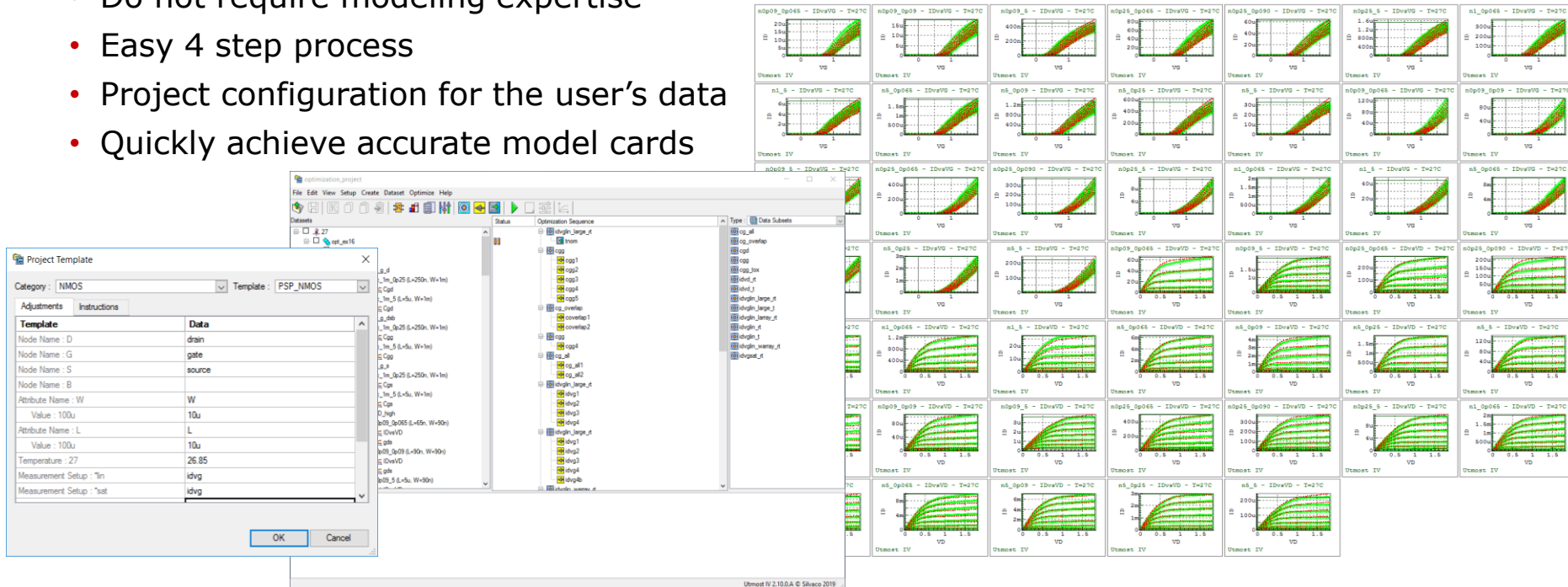


• Modeling Services



Quick-Start Optimization Templates

- Help users create optimization projects for their data
- Do not require modeling expertise
- Easy 4 step process
- Project configuration for the user's data
- Quickly achieve accurate model cards

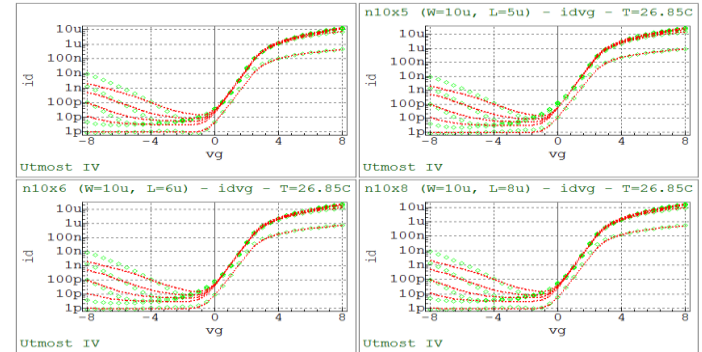
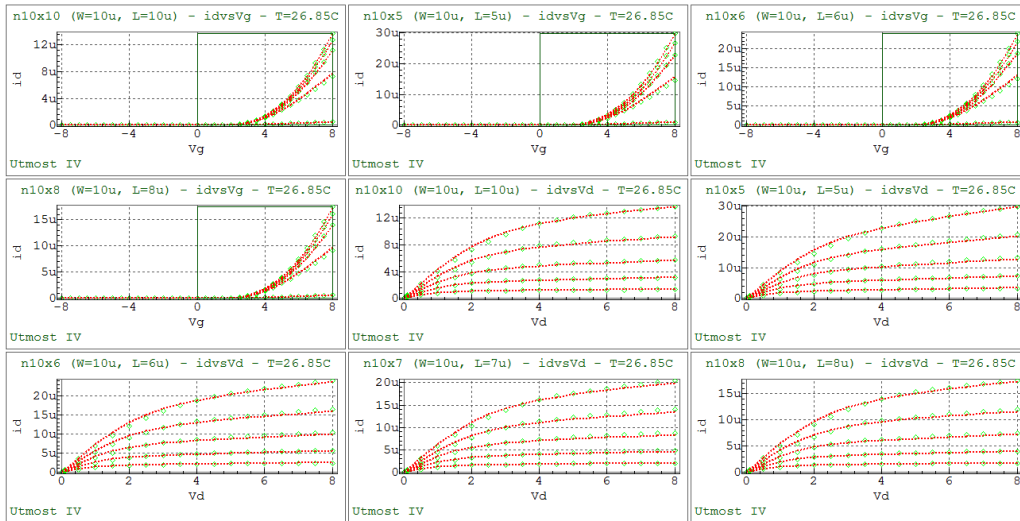


TFT Models In SmartSpice And UTMOST IV

- RPI amorphous Si TFT (Level 35), Versions 1 and 2
 - RPI poly-Si TFT (Level 36), Versions 1 and 2
 - Universal Organic TFT (UOTFT, Level 37)
 - CINVESTAV-URV Metal-Oxide TFT (MOTFT, Level 38)
 - Various custom models (Verilog-A, macromodels)
-
- Quick-Start optimization templates for RPI TFT models in UTMOST IV

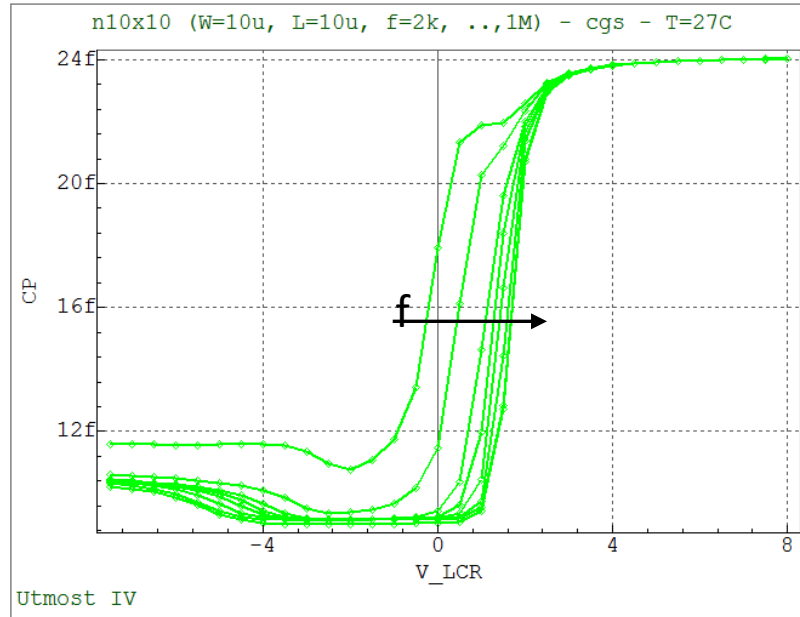
Poly-Si TFT Quick-Start Template Example

- TCAD-generated data
- 5 channel lengths
- Modeled in UTMOST IV using SmartSpice RPI Level 36 model.

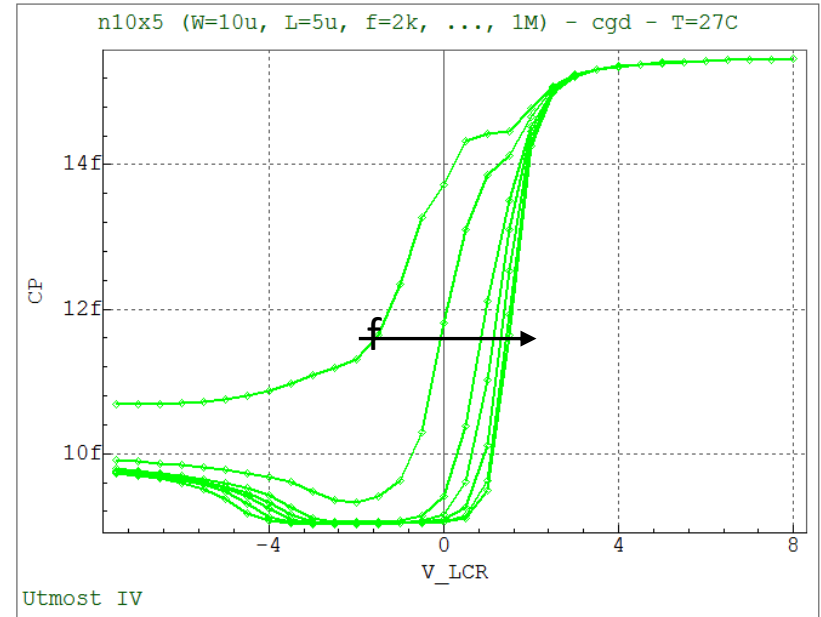


Frequency Dispersion

- Shift in C-V characteristics with frequency
- More pronounced for short channel and lower frequency



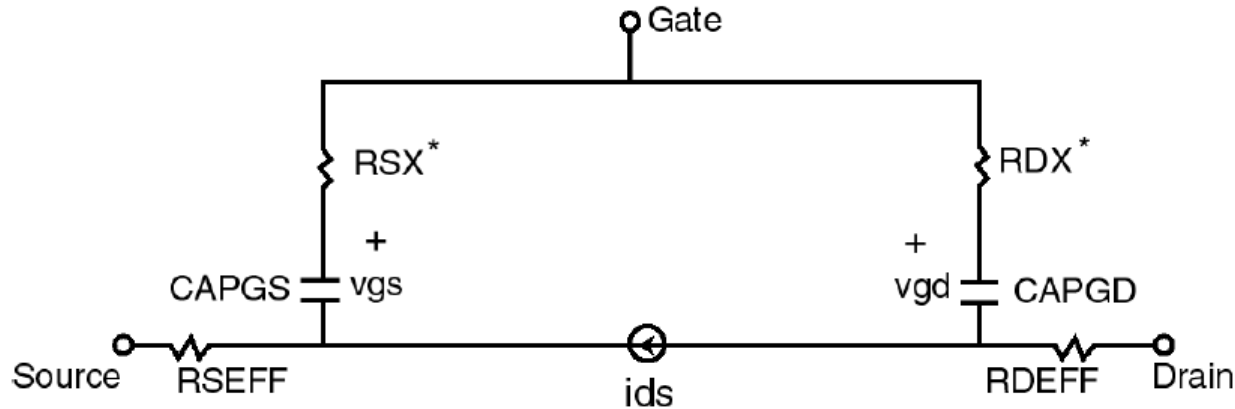
L=10um, f=2kHz, ..., 1MHz



L=5um, f=2kHz, ..., 1MHz

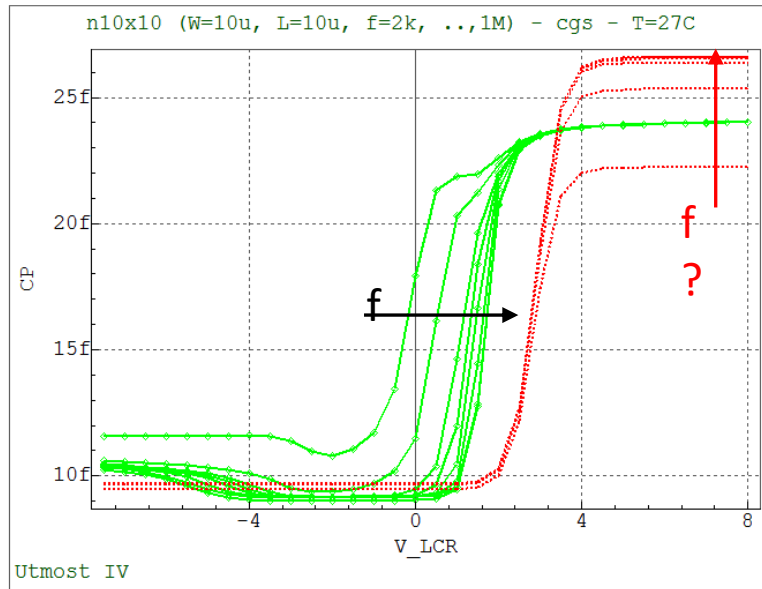
Frequency Dispersion Modeling: RPI TFT Models

- RSX and RDX elements in series with Cgs and Cgd, respectively

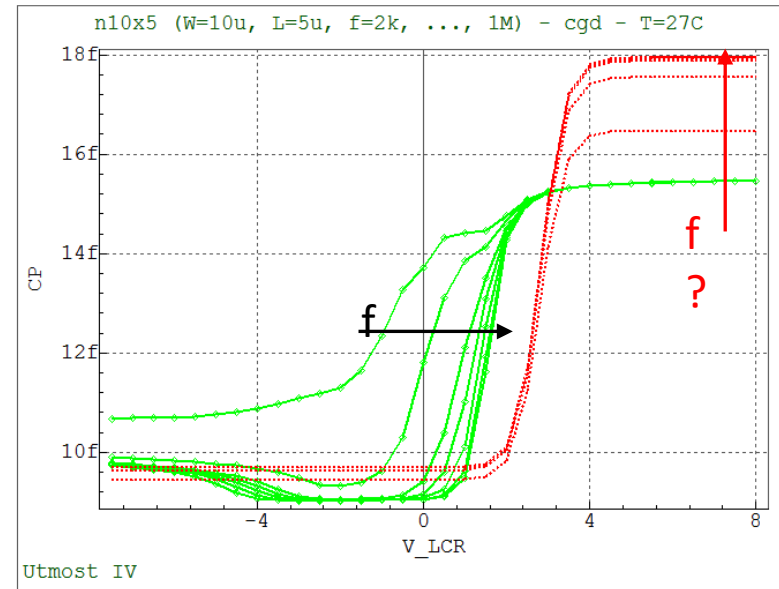


Frequency Dispersion Modeling: RPI TFT Models (cont.)

- Modeling the frequency dispersion through RSX and RDX is not adequate
- (Shifts the capacitance value instead)



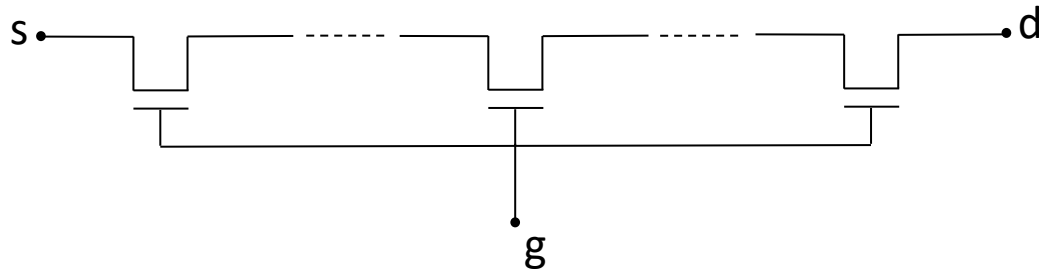
L=10um, f=2kHz, ..., 1MHz



L=5um, f=2kHz, ..., 1MHz

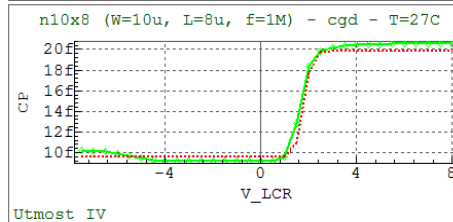
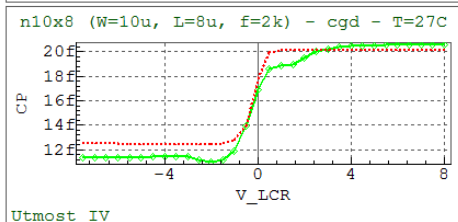
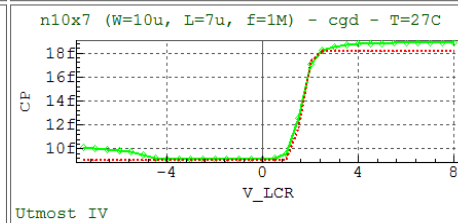
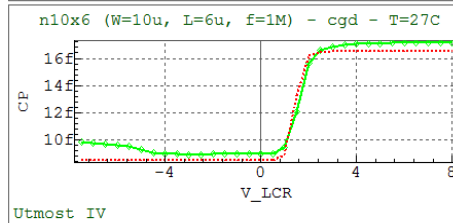
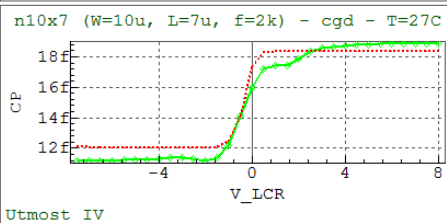
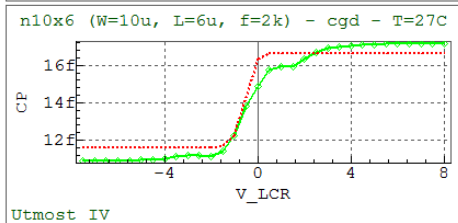
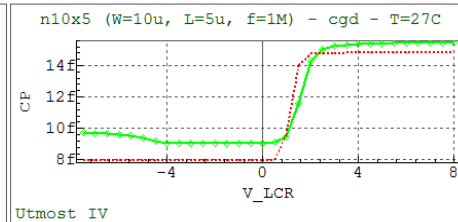
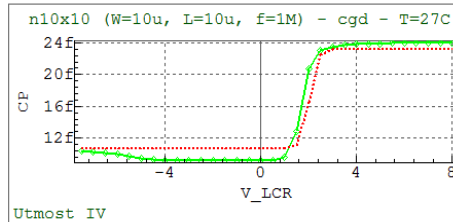
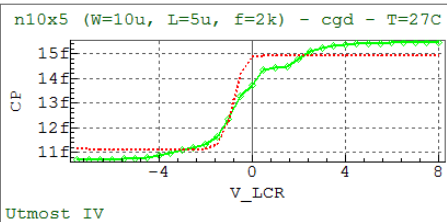
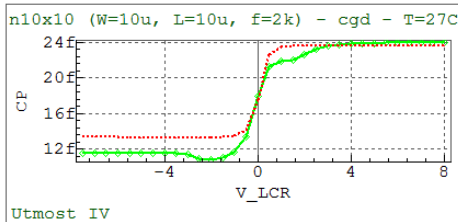
Frequency Dispersion Physical Modeling

- Due to the distributed nature of the channel
- Can be handled by effectively splitting the channel into multiple devices connected in series
- Model valid for AC as well as for transient analysis
- The number of devices: a trade-off between simulation accuracy and speed



Frequency Dispersion Modeling Results: 3 Channel Segments

- Splitting the channel into 3 devices would be a good trade-off for this

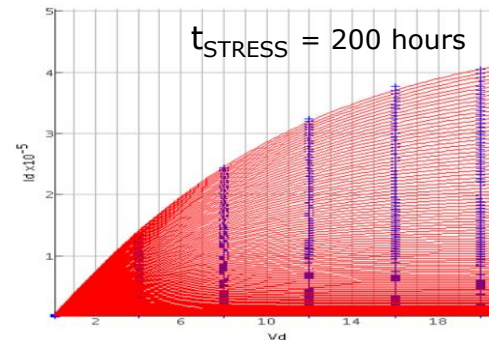
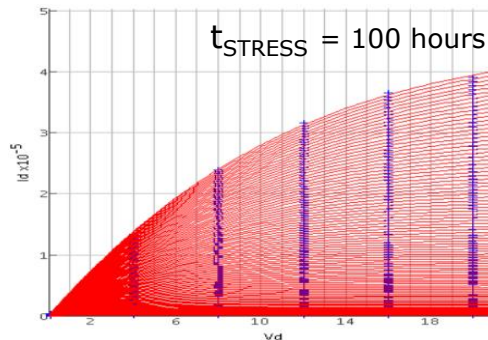
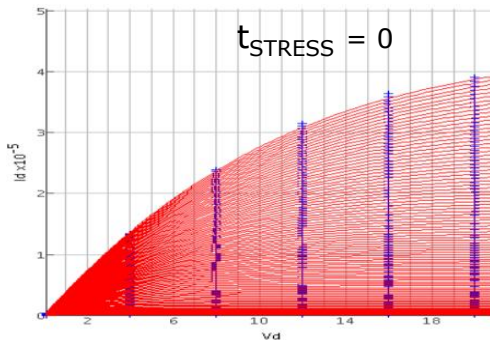
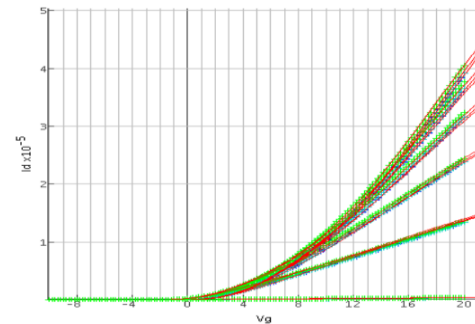
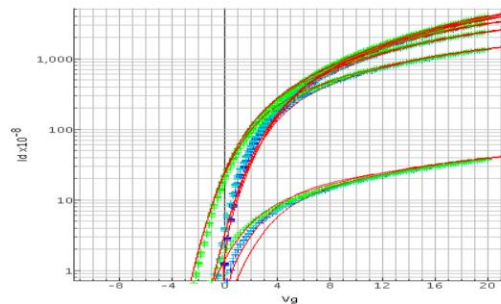


L=5um, ..., 10um, f=2kHz

L=5um, ..., 10um, f=1MHz

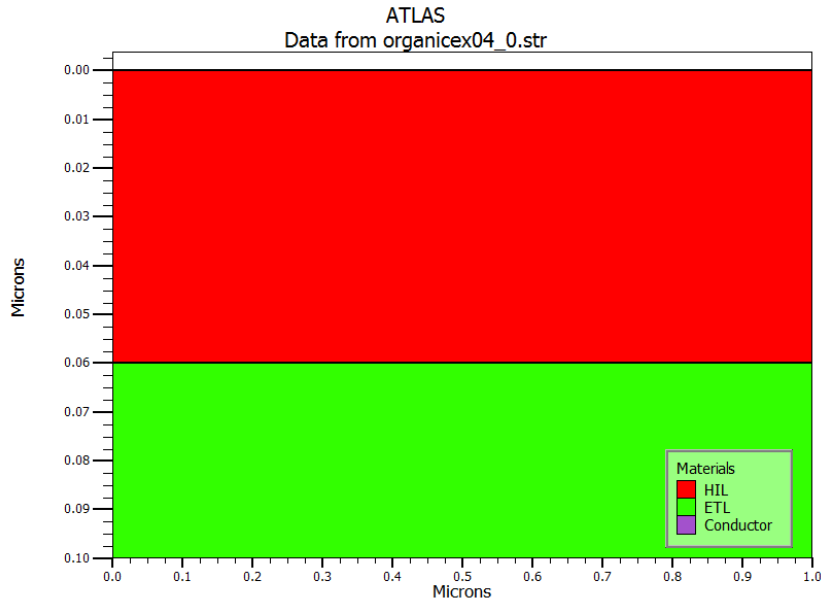
Modeling New Phenomena With TechModeler: NBIS for IGZO

- Negative Bias Illumination Stress effect on IGZO modeled using TechModeler

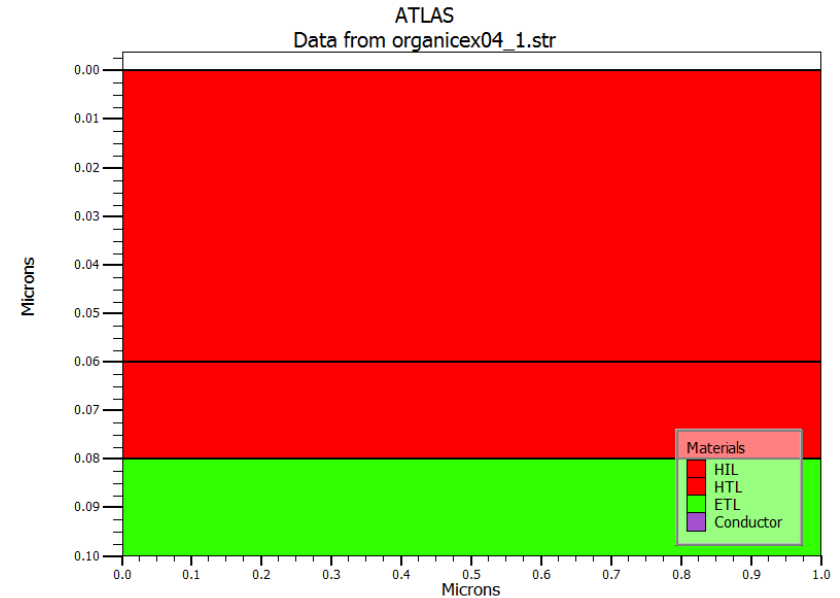


OLED Modeling

- Using TCAD-generated data to develop physical models
- Starting with two basic TCAD OLED structures, calibrated against published data



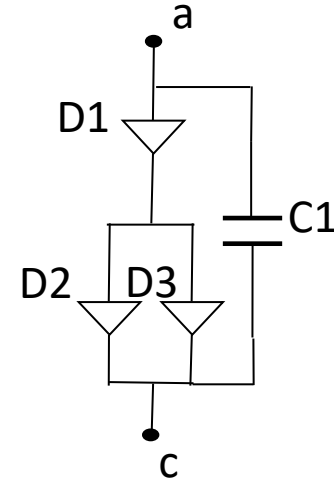
2-layer OLED



3-layer OLED

OLED SPICE Macromodel

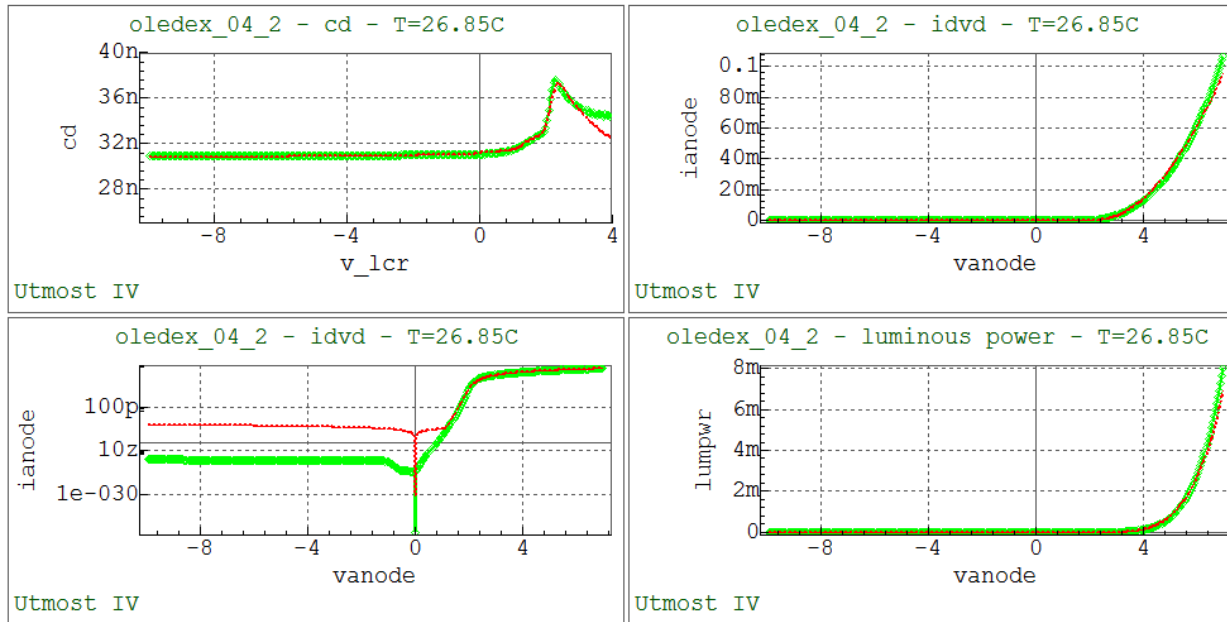
- Developing a physics-based macromodel based on the 2-layer OLED structure
- The current transport is bulk-limited and injection-limited
- These phenomena can be modeled by a regular diode D1 in series with a Fowler-Nordheim (Level 2) tunneling diode*, D2
- An additional diode, D3, is needed to compensate for the capacitance of the Fowler-Nordheim diode element.
- Additional circuit elements are used for modeling the luminous power output



*J. P. Bender et al., "OLED Modeling via SPICE", Oregon State University

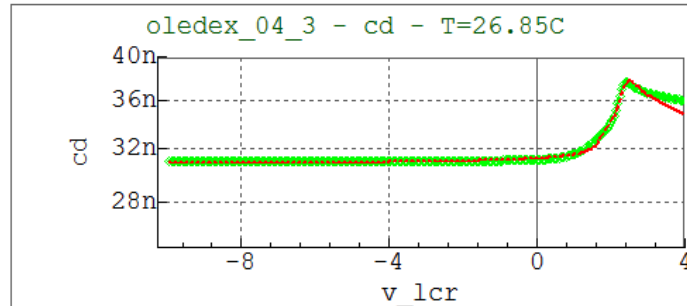
OLED Macromodel Results: 2-layer Structure

- The I-V, C-V and luminous power characteristics are accurately modeled
- If needed, the very low reverse current can be modeled using TCAD mixed-mode SPICE simulation, with extended precision

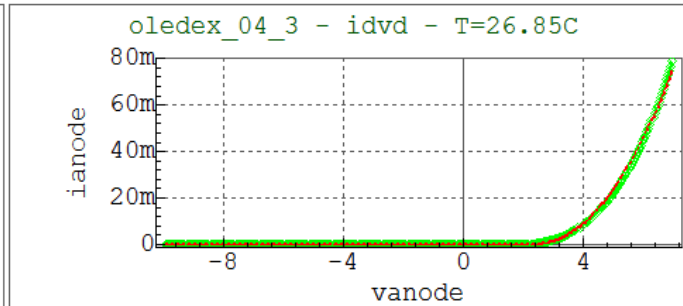


OLED Macromodel Results: 3-layer Structure

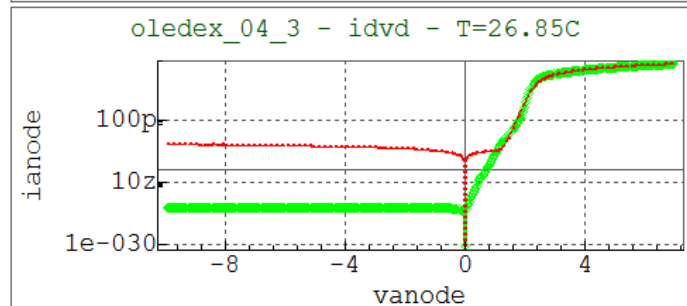
- The model developed based on the 2-layer OLED can also accurately describe the 3-layer device



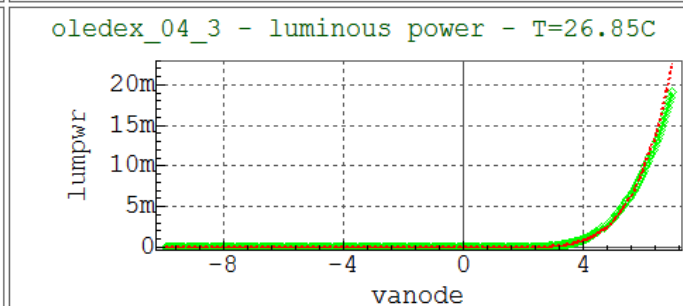
Utmost IV



Utmost IV



Utmost IV



Utmost IV

OLED Silvaco Model

- Implemented using Verilog-A
- Ongoing development
- The luminous power output can be also added, similarly to the previous example

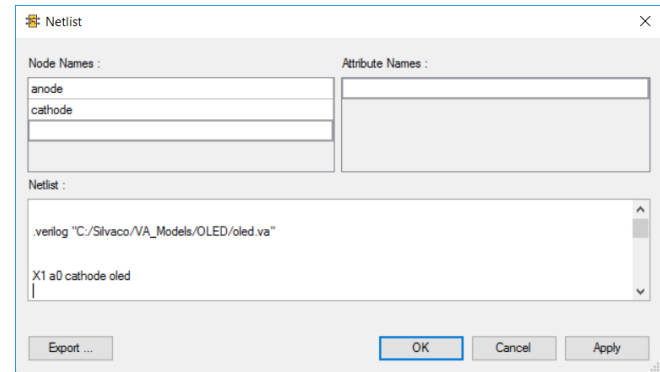
```
/* OLED model
 *
 * This implementation is
 * Copyright (C) 1984 - 2020
 * Silvaco Inc. All rights reserved
 *
 */

`include "discipline.h"
`include "constants.h"

`define EPSOX 3.453133e-11
`define N_MINLOG 1E-38
`define CHARGE 1.6021918e-19
`define K_Q (8.6170869180581252e-005)

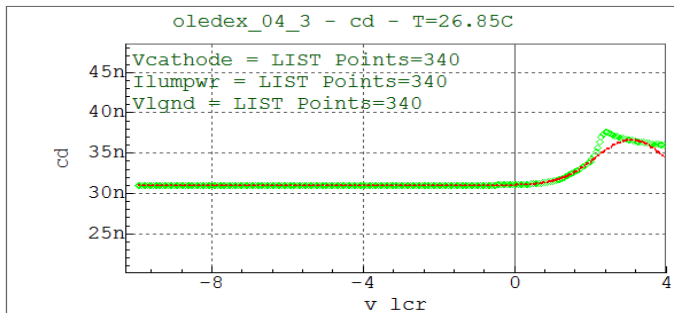
module oled(a, c);
    inout a, c;
    electrical a, c;
    electrical asw, as;

    // instance parameters
    (* desc = "Instance operating temperature difference", units = "degC" *)
    (* desc = "Instance operating temperature difference", units = "degC" *)
    (* desc = "Instance operating temperature", units = "degC" *)
```

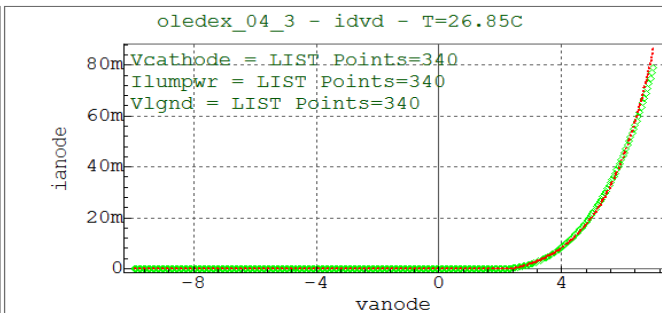


OLED Compact Model Results: 3-layer Structure

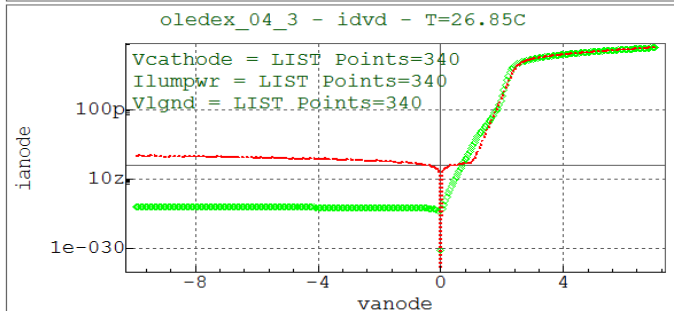
- 3-layer OLED structure characteristics using the Silvaco proprietary Verilog-A compact model



Utmost IV



Utmost IV

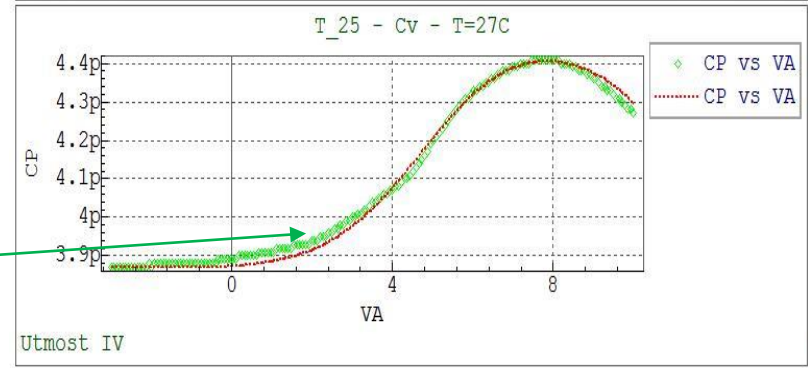
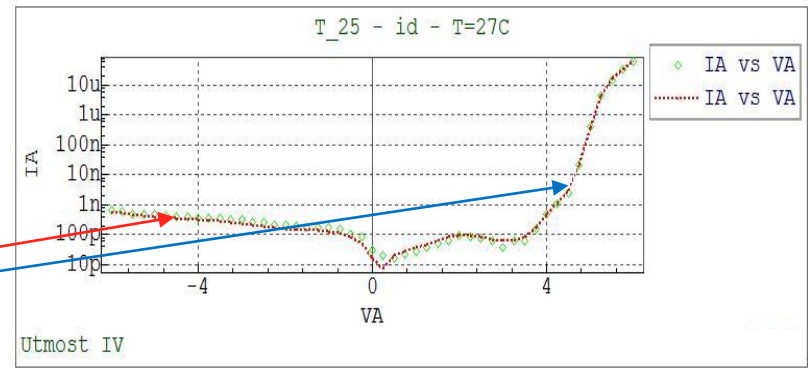


Utmost IV

Alternative OLED Modeling using UTMOST IV Verilog-A and TechModeler

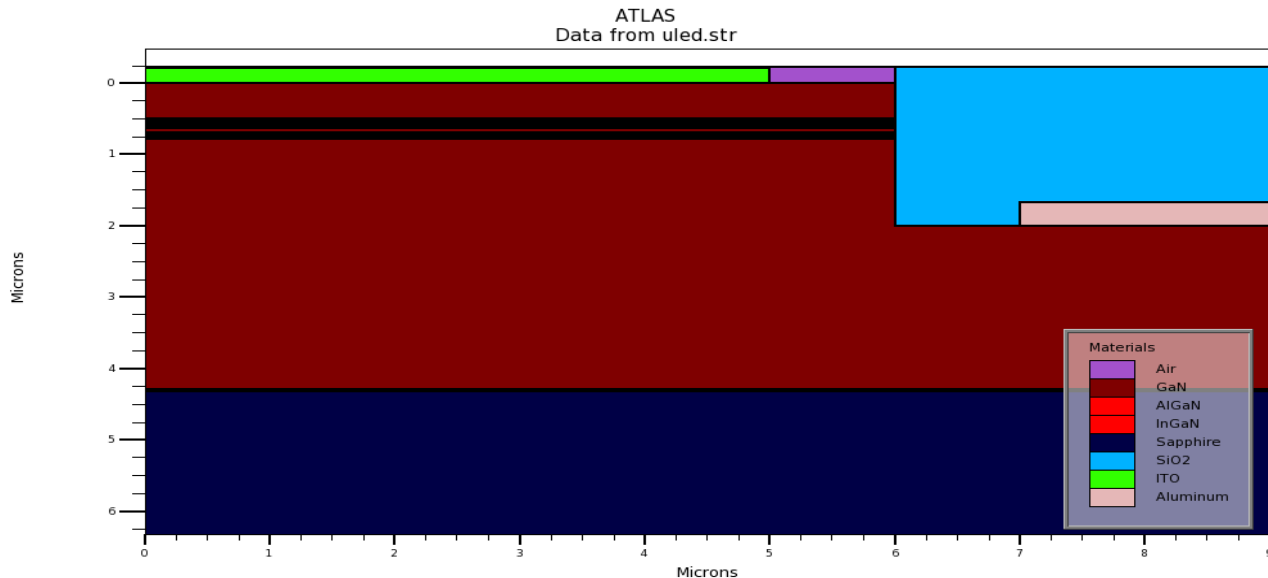
- OLED model
 - I-V model created with TechModeler
 - C-V macromodel extracted using Utmost
 - Models combined in Utmost using Verilog-A

```
include "disciplines.vams"  
include "constants.vams"  
  
module tm_model_oled(A, C);  
    include "C:\Users\bojdant\Documents\Silvaco\UTMOST4\SURGE_2017\techmodeler\vm_model1_function.v.enc"  
    include "C:\Users\bojdant\Documents\Silvaco\UTMOST4\SURGE_2017\techmodeler\tm_model14_function.v.enc"  
  
    inout A, C;  
    electrical A, C;  
  
    // Bias voltages  
    real ia;  
    real va;  
  
    // Analog block  
    analog  
    begin : the_module  
  
        // Bias dependent model evaluation  
        va = V(A,C);  
        ia = tm_vlg_model1(va) + tm_vlg_model14(va);  
        I(A,C) <- ia;  
  
    end // analog  
endmodule  
  
.verilog "C:\Users\bojdant\Documents\Silvaco\UTMOST4\SURGE_2017\techmodeler\vm_model1_function.v.enc"  
.MODEL oled VLG (  
+module = tm_model_oled  
)  
  
XOLED a c oled  
C1 a c Cval
```



Micro-LED Modeling

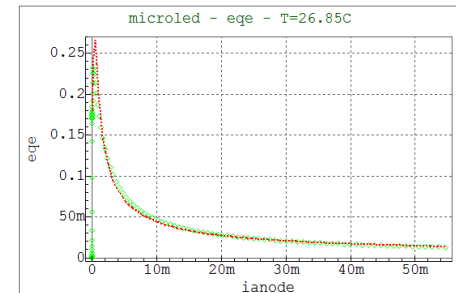
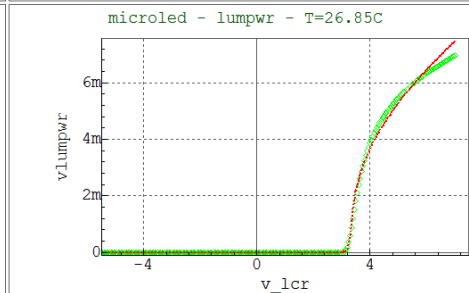
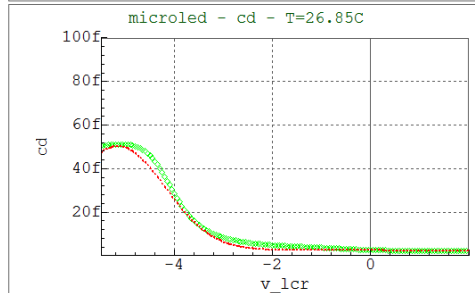
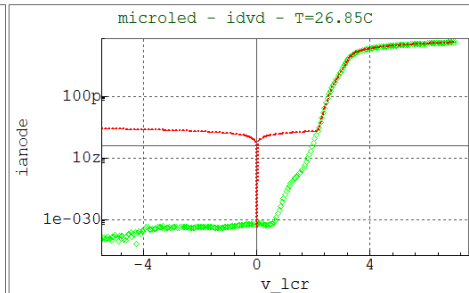
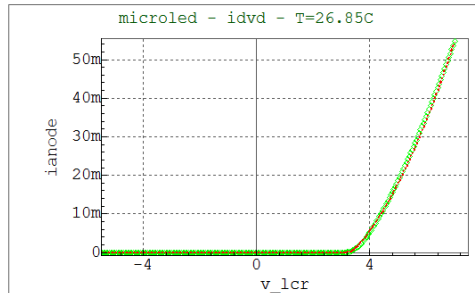
- TCAD 12 μ m Micro-LED structure
- Calibrated against published data



*H. X. Jiang et al., "III-Nitride Blue Microdisplays", Applied Physics Letters 78, 1303 (2001)

Micro-LED Compact Model Results

- Micro-LED structure characteristics using the Silvaco proprietary compact OLED model
- Added the luminous power output using a special macromodel
- Accurately describing the quantum efficiency dependence on device current.



Conclusion

- Complete modeling solution: UTMOST IV, TechModeler and modeling services
- TFT modeling capabilities of UTMOST IV and SmartSpice
- Modeling the TFT frequency dispersion effect using channel splitting
- OLED modeling examples
- Micro-LED modeling example
- Using the combined capabilities of Silvaco TCAD, UTMOST IV and SmartSpice to accurately model TFT, OLED and micro-LED devices

Thank you!